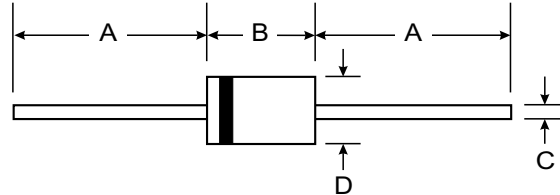


Features

- Silicon Planar Diode
- Very low reverse current
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



Mechanical Data

- **Case:** DO35 Glass case
- **Weight:** approx. 125 mg
- **Cathode Band Color:** black
- **Packaging Codes/Options:**
 TR/10 k per 13" reel (52 mm tape), 50 k/box
 TAP/10 k per Ammopack (52 mm tape), 50 k/box

DO-35		
Dim	Min	Max
A	25.40	—
B	—	4.00
C	—	0.60
D	—	2.00
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit		
Peak reverse voltage, non repetitive		V_{RSM}	140	V		
Repetitive peak reverse voltage		V_{RRM}	140	V		
Reverse voltage		V_R	125	V		
Peak forward surge current	$t_p = 1 \mu\text{s}$	I_{FSM}	2	A		
Average forward current	$f = 50 \text{ Hz}$	I_{FAV}	200	mA		
Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	$I_F = 100 \text{ mA}$	V_F			1000	mV
Reverse current	$E \leq 300 \text{ lx}, V_R$	I_R			3	nA
	$E \leq 300 \text{ lx}, V_R, T_j = 125^\circ\text{C}$	I_R			0.5	μA
	$E \leq 300 \text{ lx}, V_R = 60 \text{ V}$	I_R			1	nA
Breakdown voltage	$I_R = 5 \mu\text{A}, t_p/T = 0.01, t_p = 0.3 \text{ ms}$	$V_{(BR)}$	140			V
Diode capacitance	$V_R = 0, f = 1 \text{ MHz}$	C_D			5	pF

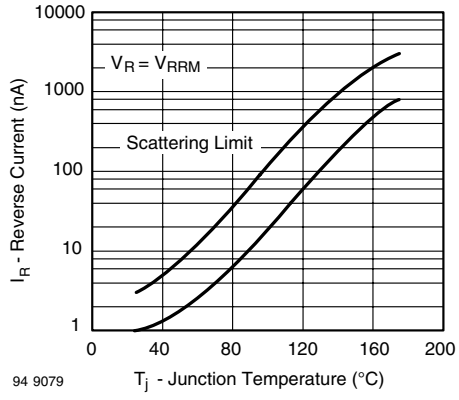


Figure 1. Reverse Current vs. Junction Temperature

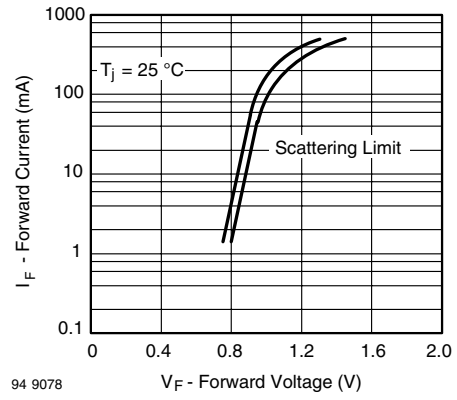


Figure 2. Forward Current vs. Forward Voltage